

RJK2009DPM

Silicon N Channel MOS FET
High Speed Power Switching

REJ03G0474-0200

Rev.2.00

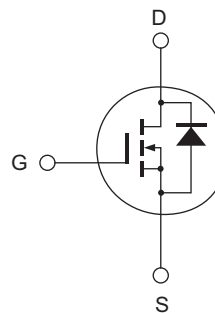
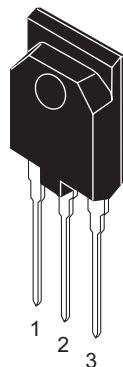
Aug.09.2005

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline

RENESAS Package code: PRSS0003ZA-A
(Package name: TO-3PFM)



1. Gate
2. Drain
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	200	V
Gate to source voltage	V_{GSS}	±30	V
Drain current	I_D	40	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	160	A
Body-drain diode reverse drain current	I_{DR}	40	A
Body-drain diode reverse drain peak current	$I_{DR(pulse)}$ ^{Note1}	160	A
Avalanche current	I_{AP} ^{Note3}	40	A
Avalanche energy	E_{AR} ^{Note3}	106	mJ
Channel dissipation	P_{ch} ^{Note2}	60	W
Channel to case thermal impedance	θ_{ch-c}	2.08	°C/W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

2. Value at $T_c = 25^\circ C$

3. $STch = 25^\circ C$, $T_{ch} \leq 150^\circ C$

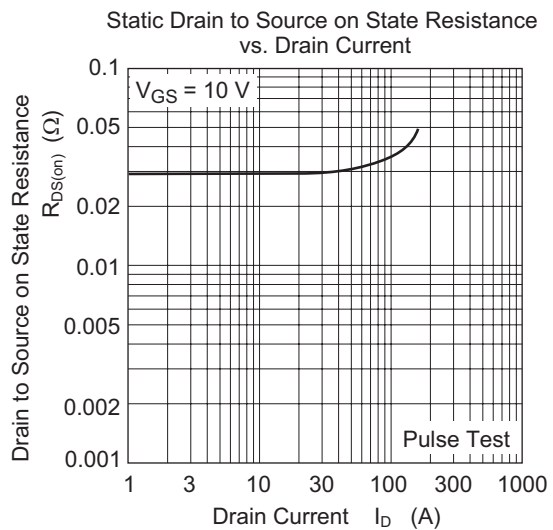
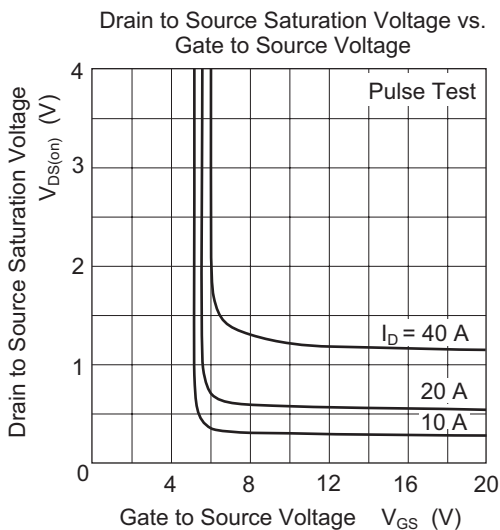
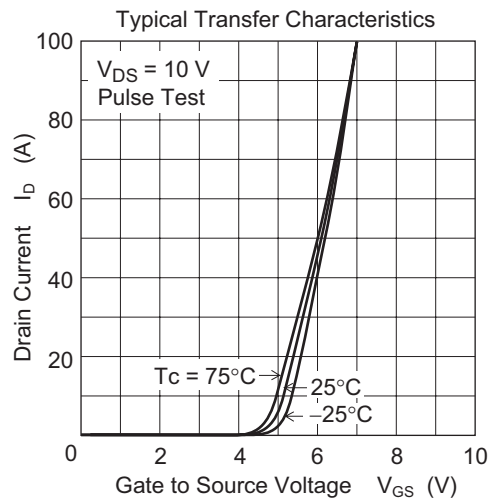
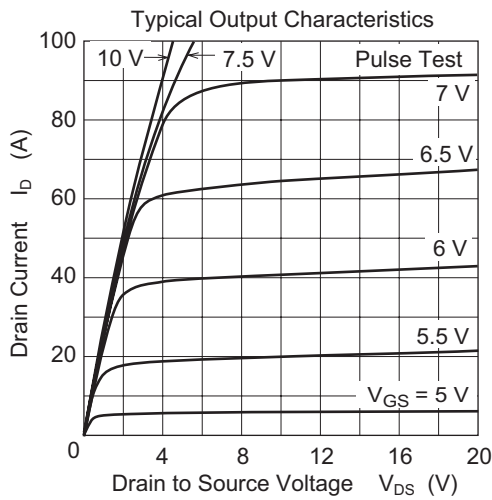
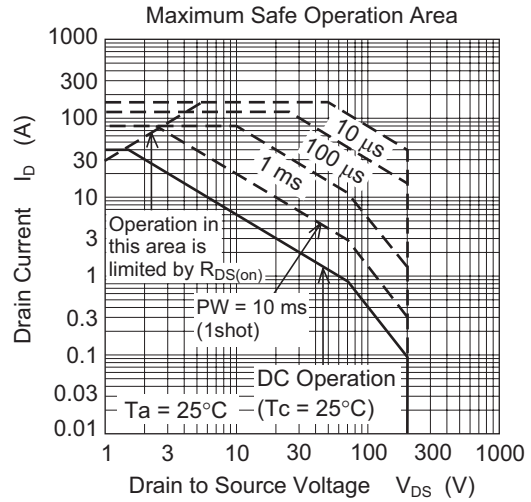
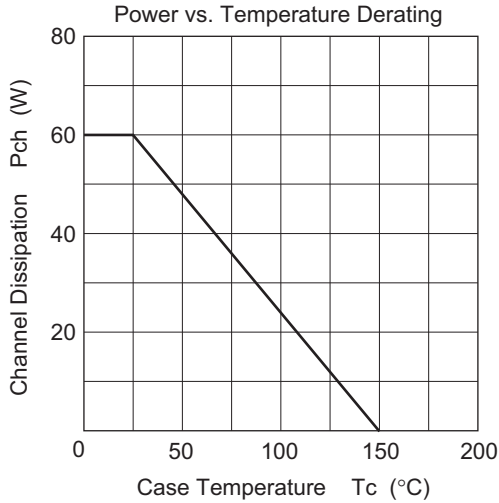
Electrical Characteristics

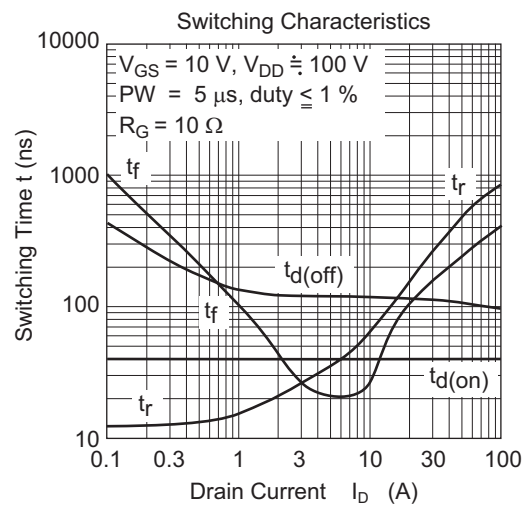
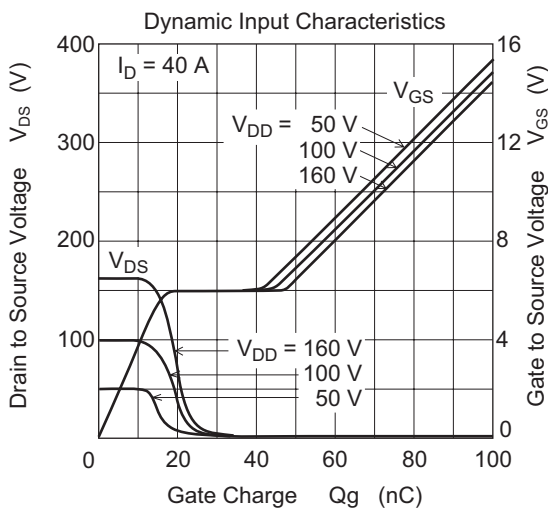
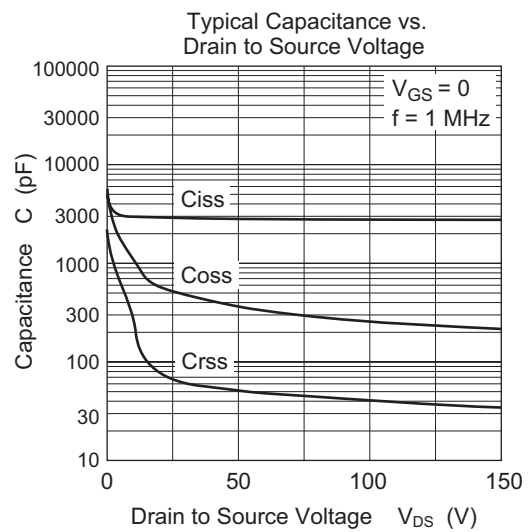
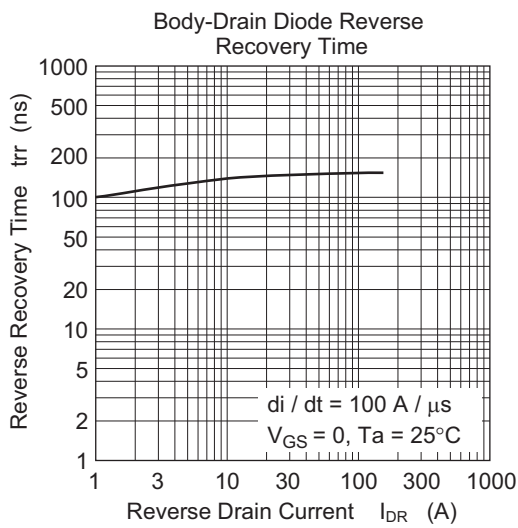
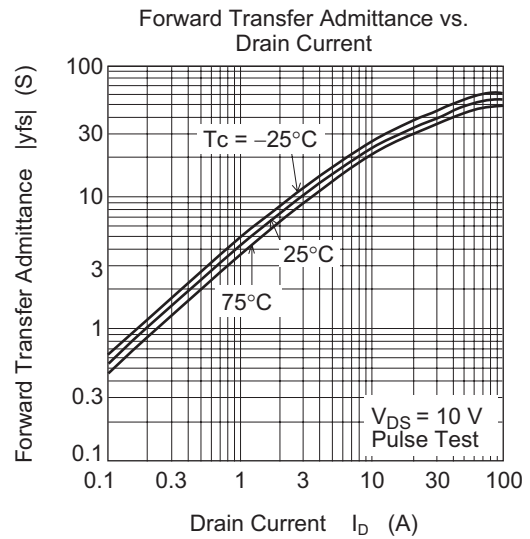
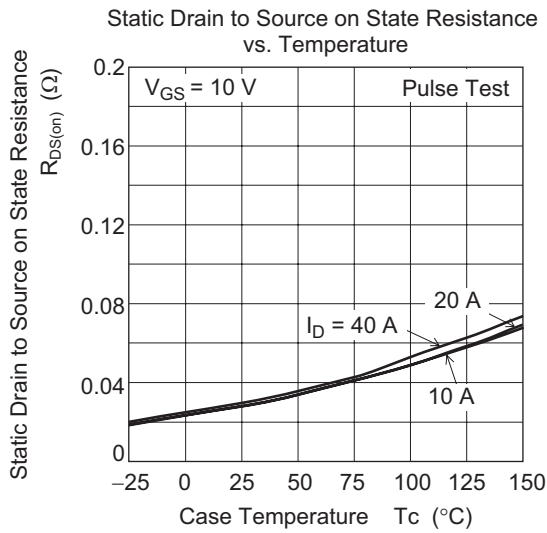
(Ta = 25°C)

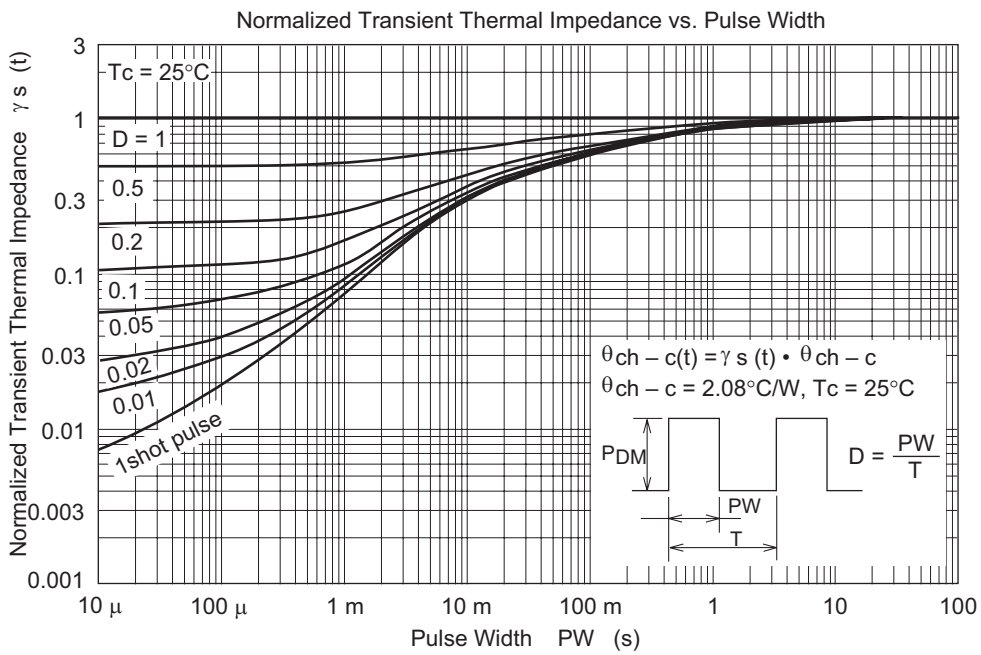
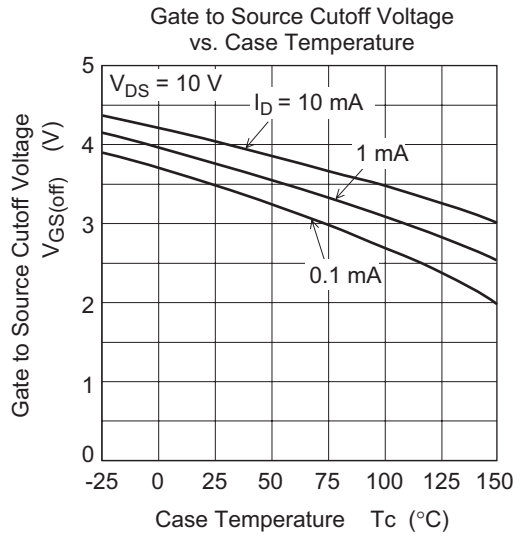
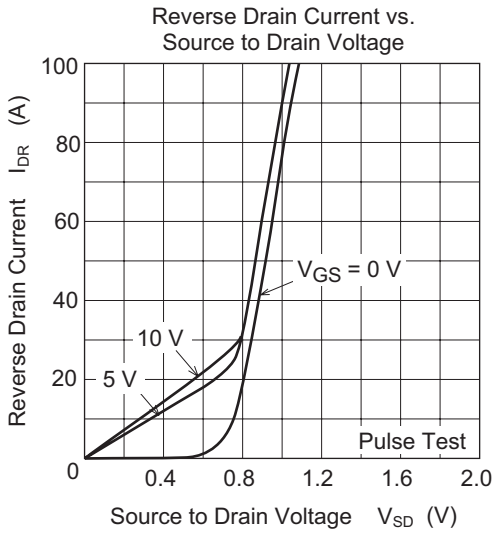
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	200	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 200 \text{ V}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	—	4.5	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Forward transfer admittance	$ y_{fs} $	20	33	—	S	$I_D = 20 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note4}
Static drain to source on state resistance	$R_{DS(on)}$	—	0.029	0.036	Ω	$I_D = 20 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	2900	—	pF	$V_{DS} = 25 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	520	—	pF	
Reverse transfer capacitance	C_{rss}	—	66	—	pF	
Turn-on delay time	$t_{d(on)}$	—	40	—	ns	$I_D = 20 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_L = 5 \Omega$, $R_g = 10 \Omega$
Rise time	t_r	—	160	—	ns	
Turn-off delay time	$t_{d(off)}$	—	120	—	ns	
Fall time	t_f	—	110	—	ns	
Total gate charge	Q_g	—	72	—	nC	$V_{DD} = 160 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 40 \text{ A}$
Gate to source charge	Q_{gs}	—	16	—	nC	
Gate to drain charge	Q_{gd}	—	31	—	nC	
Body-drain diode forward voltage	V_{DF}	—	0.9	1.4	V	$I_F = 40 \text{ A}$, $V_{GS} = 0$ ^{Note4}
Body-drain diode reverse recovery time	t_{rr}	—	150	—	ns	$I_F = 40 \text{ A}$, $V_{GS} = 0$, $diF/dt = 100 \text{ A}/\mu\text{s}$
Body-drain diode reverse recovery charge	Q_{rr}	—	0.8	—	μC	

Notes: 4. Pulse test

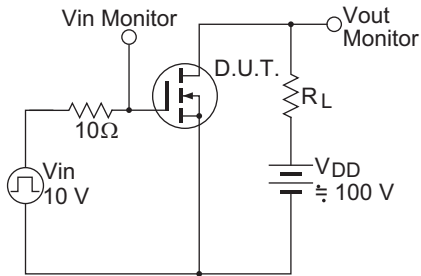
Main Characteristics



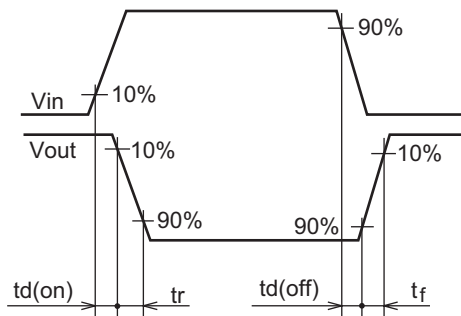




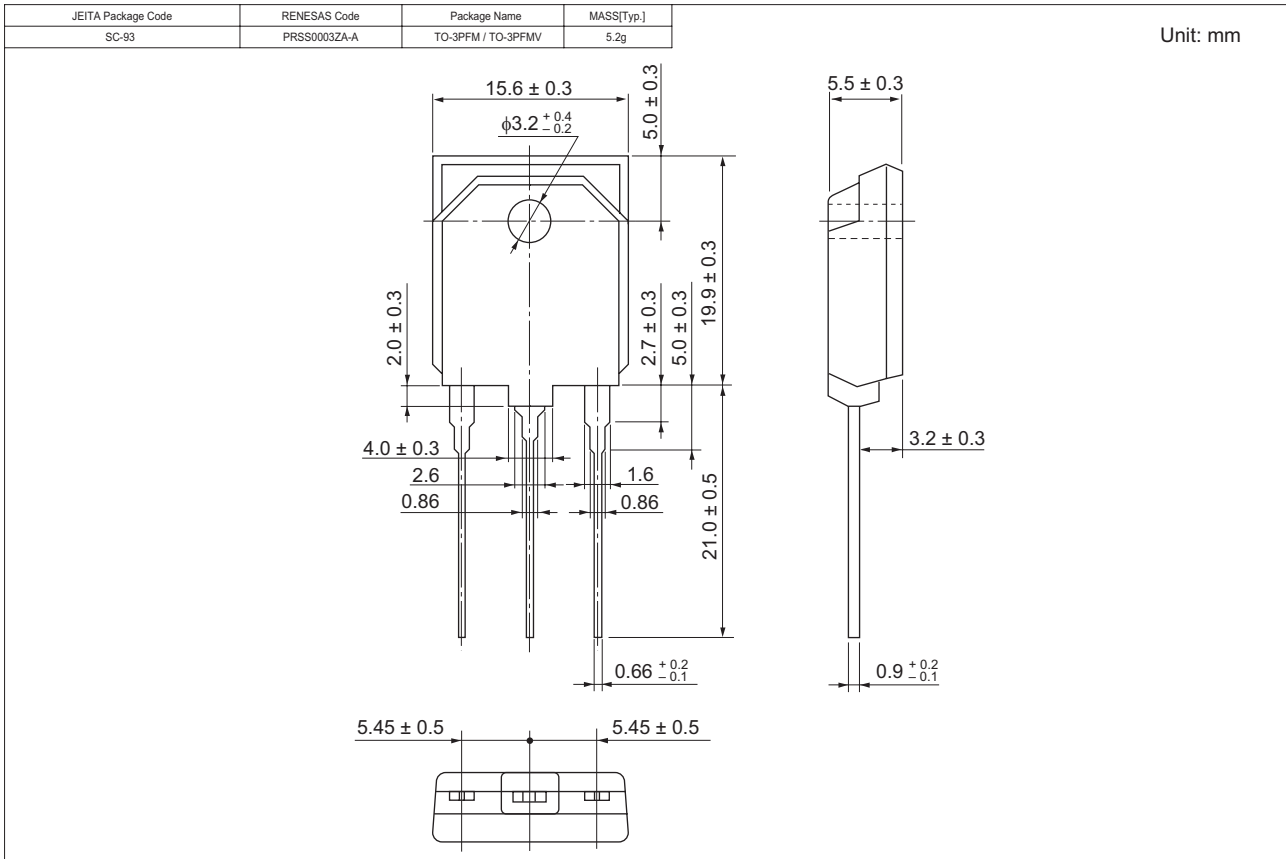
Switching Time Test Circuit



Waveform



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
RJK2009DPM-E	30 pcs	Plastic magazine

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